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FAIRCHILD SEMICONDUCTOR®

IGBT

SGH80N60UF

Ultra-Fast IGBT

General Description

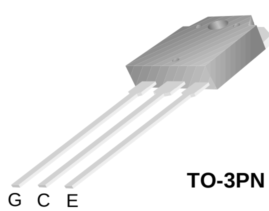
Fairchild's UF series of Insulated Gate Bipolar Transistors (IGBTs) provides low conduction and switching losses. The UF series is designed for applications such as motor control and general inverters where high speed switching is a required feature.

Features

- High speed switching
- Low saturation voltage : $V_{CE(sat)}$ = 2.1 V @ I_C = 40A
- High input impedance

Applications

AC & DC motor controls, general purpose inverters, robotics, and servo controls.



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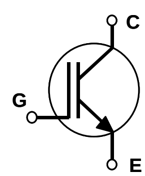

Absolute Maximum Ratings

T_C = 25°C unless otherwise noted

Symbol	Description		SGH80N60UF	Units
V_{CES}	Collector-Emitter Voltage		600	V
V_{GES}	Gate-Emitter Voltage		± 20	V
I_C	Collector Current	@ T_C = 25°C	80	A
	Collector Current	@ T_C = 100°C	40	A
$I_{CM\ (1)}$	Pulsed Collector Current		220	A
I_F	Diode Continuous Forward Current	@ T_C = 100°C	25	A
I_{FM}	Diode Maximum Forward Current		280	A
P_D	Maximum Power Dissipation	@ T_C = 25°C	195	W
	Maximum Power Dissipation	@ T_C = 100°C	78	W
T_J	Operating Junction Temperature		-55 to +150	°C
T_{stg}	Storage Temperature Range		-55 to +150	°C
T_L	Maximum Lead Temp. for Soldering Purposes, 1/8” from Case for 5 Seconds		300	°C

Notes :
(1) Repetitive rating : Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	0.64	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	40	°C/W

Electrical Characteristics of the IGBT T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV_{CES}	Collector-Emitter Breakdown Voltage	V_{GE} = 0V, I_C = 250uA	600	--	--	V
ΔB_{VCES}/ ΔT_J	Temperature Coefficient of Breakdown Voltage	V_{GE} = 0V, I_C = 1mA	--	0.6	--	V/°C
I_{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}$, V_{GE} = 0V	--	--	250	uA
I_{GES}	G-E Leakage Current	$V_{GE} = V_{GES}$, V_{CE} = 0V	--	--	± 100	nA
On Characteristics						
$V_{GE(th)}$	G-E Threshold Voltage	I_C = 40mA, $V_{CE} = V_{GE}$	3.5	4.5	6.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	I_C = 40A, V_{GE} = 15V	--	2.1	2.6	V
		I_C = 80A, V_{GE} = 15V	--	2.6	--	V
Dynamic Characteristics						
C_{ies}	Input Capacitance	V_{CE} = 30V, V_{GE} = 0V, f = 1MHz	--	2790	--	pF
C_{oes}	Output Capacitance		--	350	--	pF
C_{res}	Reverse Transfer Capacitance		--	100	--	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{CC} = 300 V, I_C = 40A, R_G = 5Ω, V_{GE} = 15V, Inductive Load, T_C = 25°C	--	23	--	ns
t_r	Rise Time		--	50	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	90	130	ns
t_f	Fall Time		--	50	150	ns
E_{on}	Turn-On Switching Loss		--	570	--	uJ
E_{off}	Turn-Off Switching Loss		--	590	--	uJ
E_{ts}	Total Switching Loss		--	1160	1500	uJ
$t_{d(on)}$	Turn-On Delay Time	V_{CC} = 300 V, I_C = 40A, R_G = 5Ω, V_{GE} = 15V, Inductive Load, T_C = 125°C	--	30	--	ns
t_r	Rise Time		--	55	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	150	200	ns
t_f	Fall Time		--	160	250	ns
E_{on}	Turn-On Switching Loss		--	630	--	uJ
E_{off}	Turn-Off Switching Loss		--	940	--	uJ
E_{ts}	Total Switching Loss		--	1580	2000	uJ
Q_g	Total Gate Charge	V_{CE} = 300 V, I_C = 40A, V_{GE} = 15V	--	175	250	nC
Q_{ge}	Gate-Emitter Charge		--	25	40	nC
Q_{gc}	Gate-Collector Charge		--	60	90	nC
L_e	Internal Emitter Inductance	Measured 5mm from PKG	--	14	--	nH

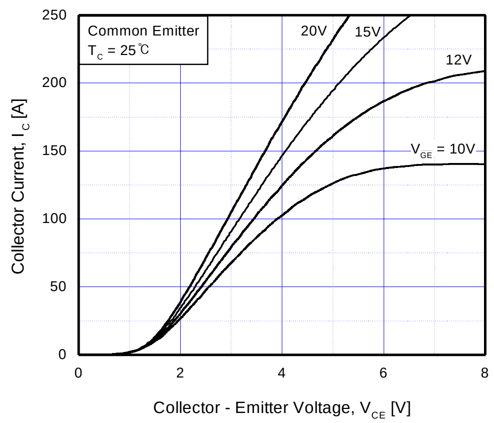

Fig 1. Typical Output Characteristics

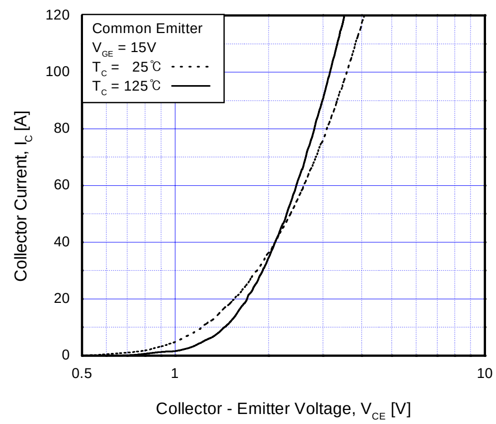

Fig 2. Typical Saturation Voltage Characteristics

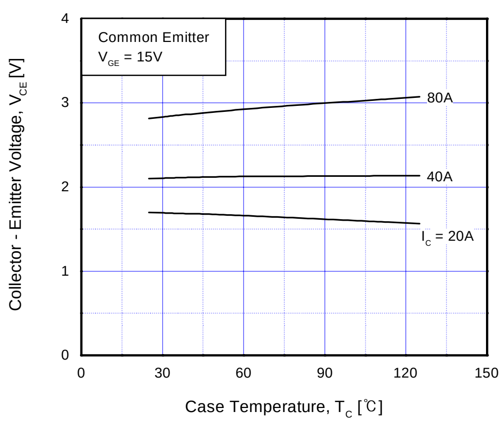

Fig 3. Saturation Voltage vs. Case Temperature at Variant Current Level

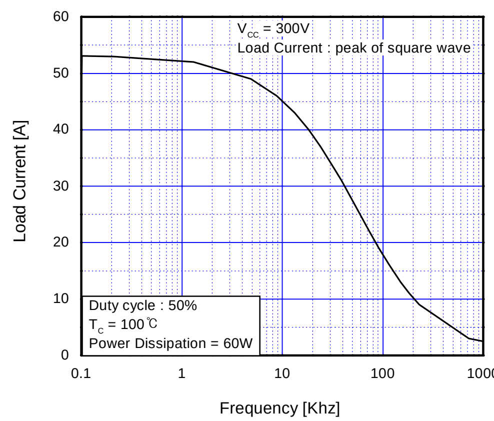

Fig 4. Load Current vs. Frequency

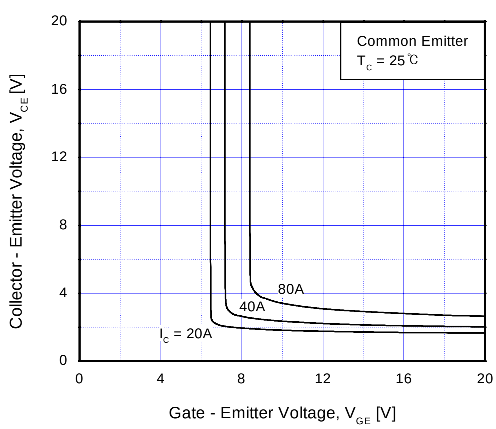

Fig 5. Saturation Voltage vs. V_{GE}

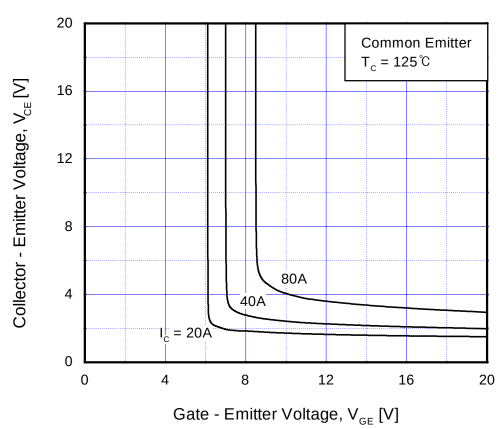

Fig 6. Saturation Voltage vs. V_{GE}

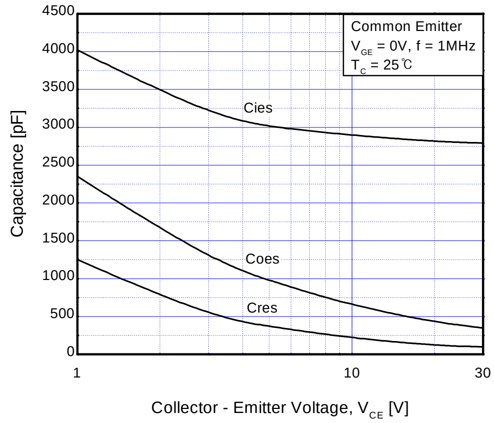

Fig 7. Capacitance Characteristics

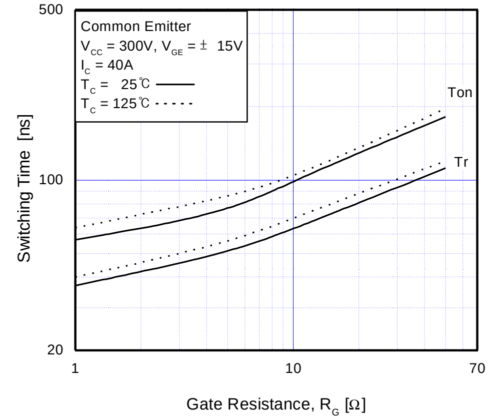

Fig 8. Turn-On Characteristics vs. Gate Resistance

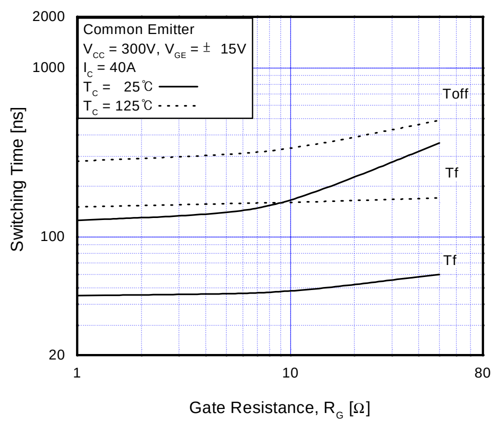

Fig 9. Turn-Off Characteristics vs. Gate Resistance

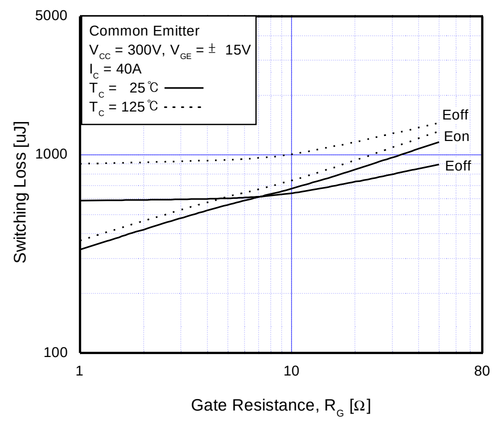

Fig 10. Switching Loss vs. Gate Resistance

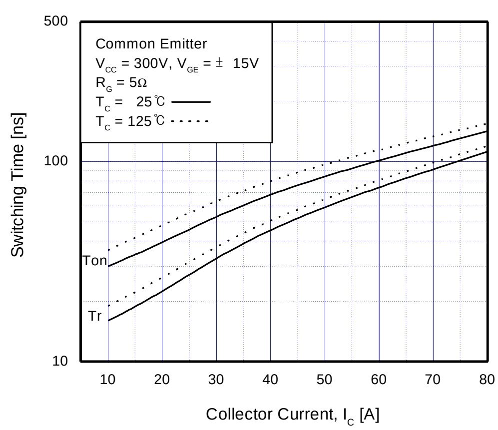

Fig 11. Turn-On Characteristics vs. Collector Current

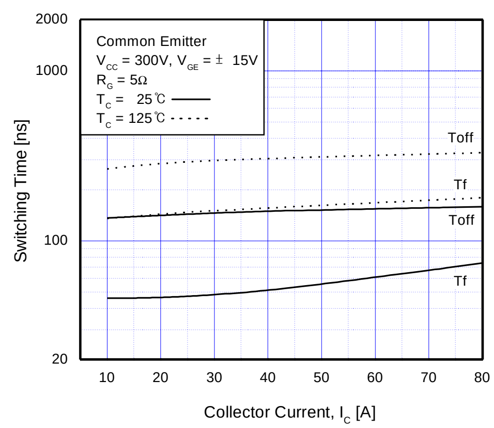

Fig 12. Turn-Off Characteristics vs. Collector Current

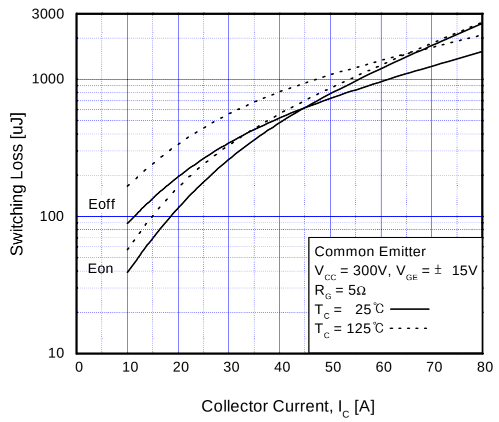

Fig 13. Switching Loss vs. Collector Current

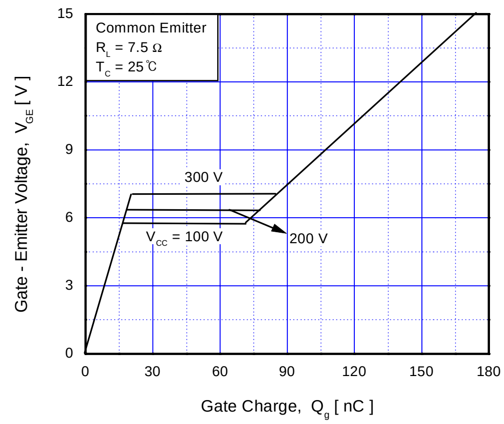

Fig 14. Gate Charge Characteristics

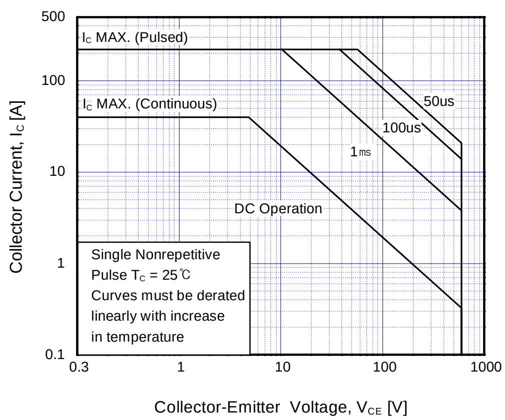

Fig 15. SOA Characteristics

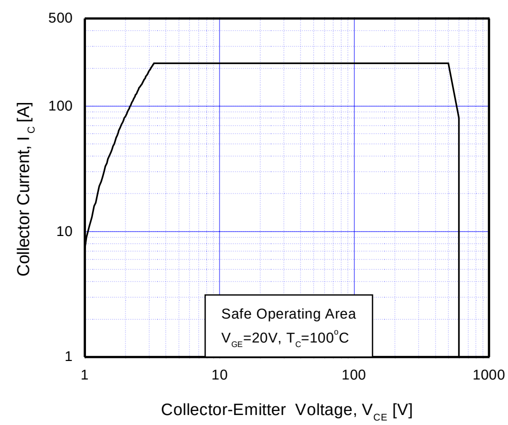

Fig 16. Turn-Off SOA Characteristics

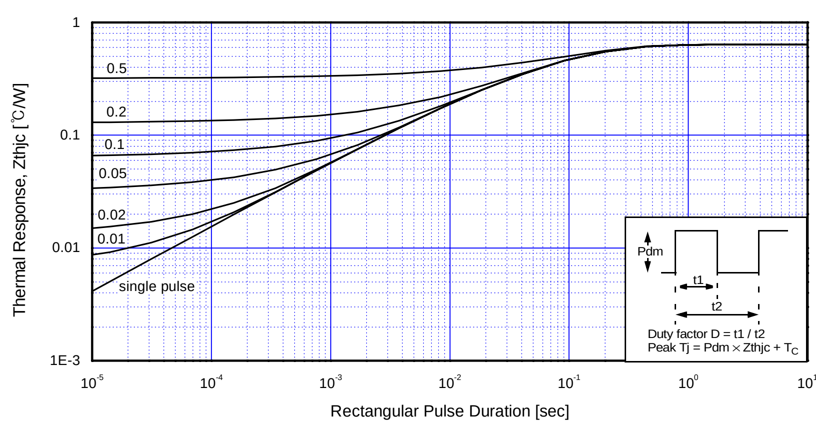

Fig 17. Transient Thermal Impedance of IGBT

Mechanical Dimensions

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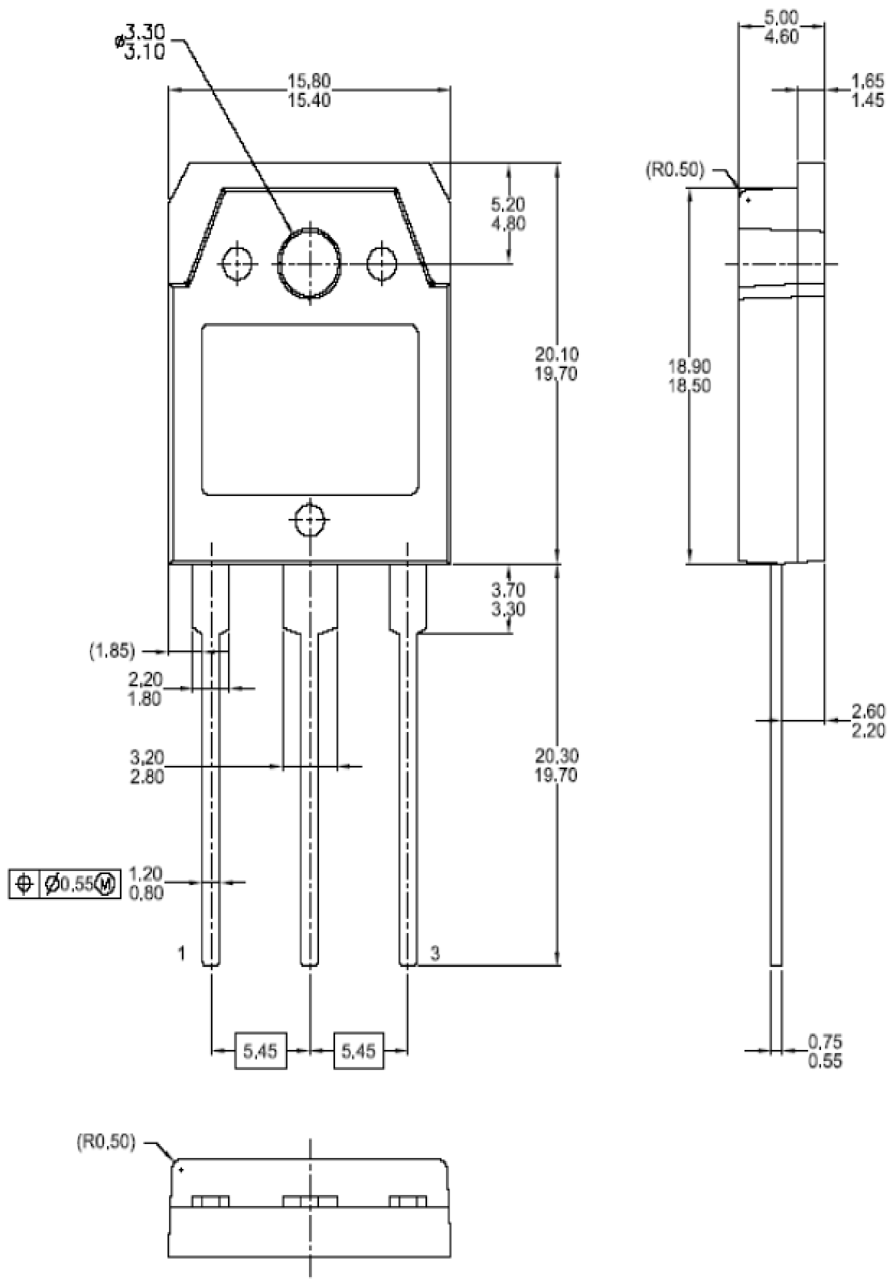

Dimensions in Millimeters

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